

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AJT015** is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	1.8 A
<b>V<sub>CC</sub></b>	32 V
<b>P<sub>DISS</sub></b>	50 W @ T <sub>C</sub> ≤ 100 °C
<b>T<sub>J</sub></b>	-65 °C to +250 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	3.0 °C/W

**PACKAGE STYLE .310 2L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.286 / 7.26	.306 / 7.77
E	.110 / 2.79	.130 / 3.30
F	.306 / 7.77	.318 / 8.08
G	.148 / 3.76	
H	.400 / 10.16	
I	.119 / 3.02	
J	.552 / 14.02	.572 / 14.53
K	.790 / 20.07	.810 / 20.57
L	.300 / 7.62	.320 / 8.13
M	.003 / 0.08	.006 / 0.15
N	.052 / 1.32	.072 / 1.83
P	.118 / 3.00	.131 / 3.33
R		.230 / 5.84

**ORDER CODE: ASI10545**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 10 mA	55			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 10 mA      R <sub>BE</sub> = 10 Ω	55			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 28 V      V <sub>BE</sub> = 0 V			2.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 500 mA	15		150	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 45 V      P <sub>OUT</sub> = 15 W      f = 960 - 1215 MHz	8.1			<b>dB</b>
<b>η<sub>C</sub></b>		40			<b>%</b>